

# LUMPED ELEMENTS AND ITS EXISTENCE IN QUASI LUMPED ELEMENT RESONATOR ANTENNA

## Abstract

In this paper, the Quasi Lumped Element Resonator Antenna is reviewed. It is composed of Lumped elements. Lumped Elements are passive components whose size across any dimensions should be small to make it a lumped element. The various researches that have been done to come about the various types of basic building blocks of the lumped element are staged in this write up. This review is towards accomplishing the derivation of the component elements used in the design of the Quasi Lumped Element Resonator Antenna. These elements are the interdigital capacitor, inductor and pad capacitors. The pertinent formulae for determining each one of them were all expressed in this review. The formula for calculating the resonance frequency of the Quasi Lumped Element Resonator Antenna was expressed in this review. The equivalent circuit model for the lumped elements were all reviewed and presented. This review brings about how the lumped elements are involved in the design of the Quasi Lumped Element Resonator Antenna.

**Keywords-** Lumped Element, Frequency, Quasi Lumped Element Resonator Antenna.

## 1.0 Introduction

Devices capable of radiating and receiving radio waves are known as antennas (Balanis, 2016). They are at the interface between free space and the guiding device. The guiding device is the transmission line through which an electrical signal travels before conversion into electromagnetic waves or radiation energy for transmission or transportation through free space.

Antennas are of a variety of types with each having different shapes. These include wire antenna, microstrip patch antenna, reflector antenna, array antenna, lens antenna, aperture antenna and Quasi Lumped Element Resonator Antenna. Quasi Lumped Element Resonator Antenna is an exception in its design behavior because its resonance frequency depends on some lumped element components. These makes it to have a high degree of freedom and flexibility.

Quasi lumped Element Resonator antenna is made up of lumped capacitor, lumped inductors. By understanding the behavior of these lumped elements, the antenna behavior can be predicted. Lumped elements are passive components in microwave circuits whose size across any dimension is much smaller than the operating wavelength to ensure that there is no appreciable phase shift between the input and output terminals. When using lumped elements at RF and microwave frequencies, the maximum dimensions for these components should be about  $\lambda/20$ , where  $\lambda$  is the guide wavelength (Bahl, 2003). Lumped elements circuits can be divided as shown in Figure 1.0

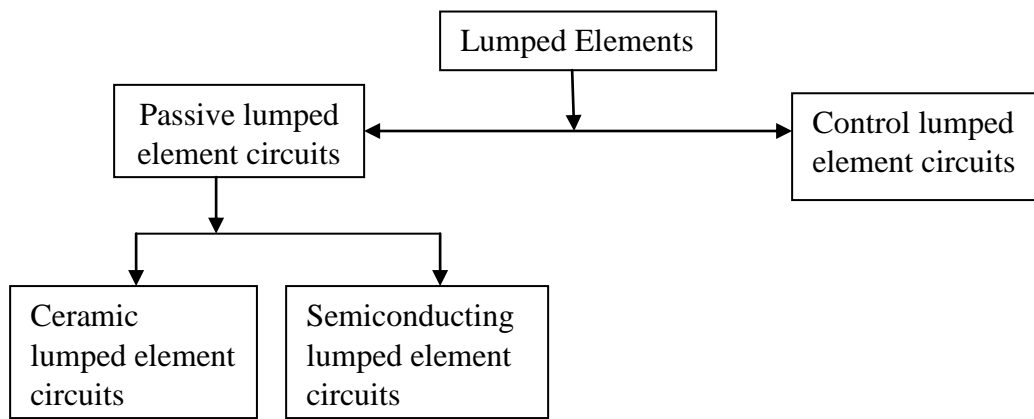


Figure 1.0: Division of Lumped Elements in Microwave Circuit

The lumped element circuit is a ceramic lumped element circuit if thick film printed inductors and discrete capacitors are used, while it is a semiconductor lumped element circuits when High Temperature Semiconductors (HTSs) are used in its design instead of the Duroid Microwave substrate (Bahl, 2003).

Figure 1.1 shows the basic building blocks from which lumped elements are derived and some commonly used components

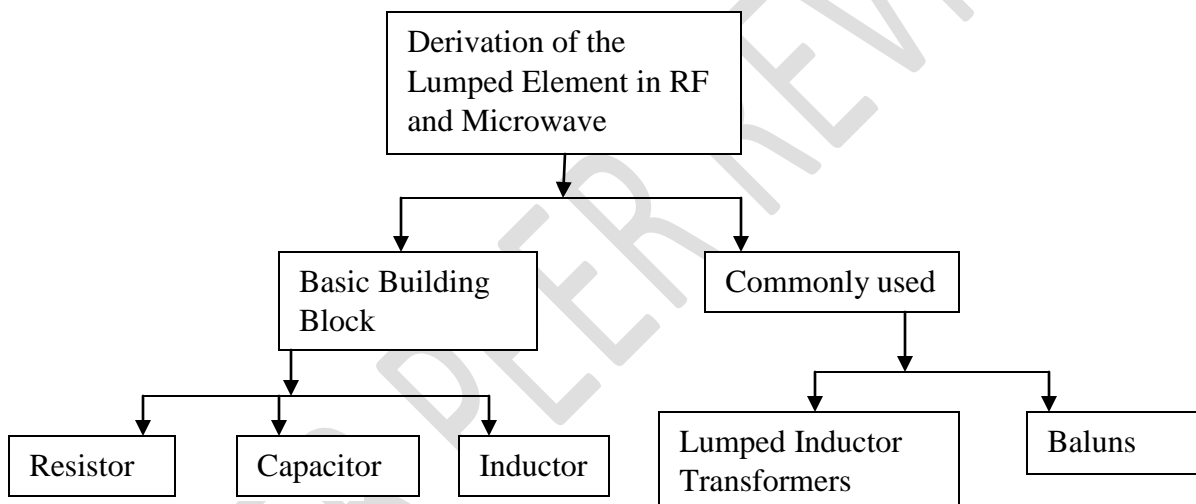


Figure 1.1: Lumped Elements in RF and Microwave Circuits

From Figure 1.1, the basic building blocks of lumped element in RF and microwave circuits are the resistor, capacitor and inductor. While the commonly used are Lumped inductor transformers and baluns (Bahl, 2003)

### 1.1 Basic Circuit Elements of the Lumped Element

In this subsection a brief review of the basic mathematical relationship between the terminal voltage and current across each of the circuit elements is described.

This review is necessary as it serves as the background for this study. Consider that these elements (Inductor,  $L$ ; Capacitor  $C$ ; and Resistor  $R$ ) as shown in Figure 2.8 are ideal (pure and linear).

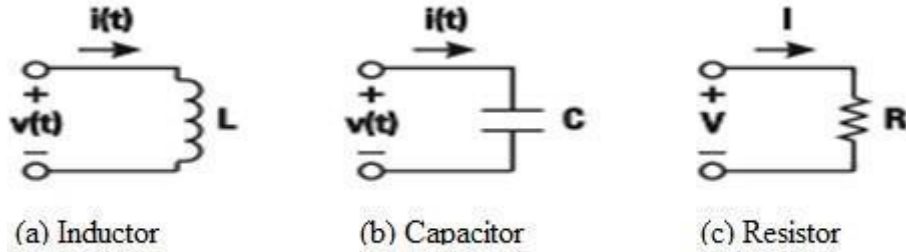


Figure 1.3: Two-Terminal Voltage and Current Representation of Lumped Elements (Bahl, 2003).

In Figure 1.3 (a), an ideal inductor of inductance  $L$  is depicted,  $i(t)$  is the time-varying current passed through the inductor of inductance  $L$  and  $v(t)$  is voltage across its terminals. The inductor stores or releases magnetic energy  $W_m$  and does not store electric energy. The inductor does not dissipate any power and the phase of the time-varying current  $i(t)$  lags the phase of the voltage  $v(t)$  across its terminals. This is stated mathematically as follow (Bahl, 2003):

$$V_{(t)} = L \frac{di_{(t)}}{dt} \quad (1.0)$$

$$V = j\omega L I \quad (1.1)$$

$$I_{(t)} = \left(\frac{1}{L}\right) \int V_{(t)} dt \quad (1.2)$$

$$I = \frac{v}{j\omega L} \quad (1.3)$$

$$W_m = \frac{1}{2} * L i_0^2 \quad (1.4)$$

In equations (1.0) to (1.4), the time dependence is assumed to be  $e^{j\omega t}$  and  $i_0$  is the root mean square (rms) value of the current.

Figure 1.3(b) depicts an ideal capacitor of capacitance  $C$ .  $i(t)$  is the time-varying current passed through the capacitor  $C$  and  $v(t)$  is voltage across its terminals. The capacitor of capacitance  $C$  in Figure 1.3(b) stored or released energy but only of electric type. The capacitor does not dissipate any power and the phase of the time-varying current  $i(t)$  leads the phase of the voltage  $v(t)$  across its terminals. This is stated mathematically as follows (Bahl, 2003):

$$I_{(t)} = C * \frac{dv_{(t)}}{dt} \quad (1.5)$$

$$I = j\omega C V \quad (1.6)$$

$$V_{(t)} = \frac{1}{c} * \int i_{(t)} dt \quad (1.7)$$

$$W_e = C V_0^2 \quad (1.8)$$

where

$v_0$  is the rms value of the voltage.

104

105 A linear resistor is a lossy component whose dimensions are much less than the operating  
106 wavelength. In this component, the voltage applied to its terminals and the current passing  
107 through the resistor are in phase and the incident power is completely dissipated. Let  $V$  and  $I$  be  
108 the rms voltage and current across a resistor of value  $R$ , therefore, Ohm's law is stated as:

109 
$$V=RI \tag{1.9}$$

110 And the power dissipated is given as:

111 
$$P=IV \tag{1.10}$$

## 112 2.0 Lumped Element Modeling

113 In order to use lumped elements correctly, the idea about how the lumped elements are modeled  
114 should be known. At RF and microwave frequencies, to model this lumped elements, they are  
115 realized based on a maximum dimension of one-twentieth of a wavelength, which is based on a  
116 small section of a microstrip line. The design is done by selecting a suitable length of each  
117 section. The lumped capacitor can be realized by using an open circuited ( $Z_L = \infty$ ) microstrip  
118 sections and a lumped inductor is realizable using a short circuited ( $Z_L = 0$ ) microstrip section.  
119 Thus, a small section of the short circuited transmission line behaves as a lumped inductor in  
120 series with a resistance  $R$  (Rafiee, 2015). It is a lumped inductor if the value of the resistance is  
121 very small, but where the conductor used in designing the lumped element is Nicr (gold), the  
122 value of the resistance is high and the lumped element is resistive. The proportional value of the  
123 resistance, inductance, and capacitance components depend on the use of the lumped element. If  
124 the short circuited line has zero resistance in series with the inductor. The short circuited  
125 microstrip line then behaves as an inductor, otherwise when the resistance is very high, as in the  
126 case of an inductor in series with a high resistance, for example when Nicr (gold) is used as the  
127 conductor, the microstrip section behaves as a resistor (Olokede, 2013). These

128 small sections are called quasi-lumped elements at High Frequency (HF) since the sections are  
129 used to replace the actual lumped elements (Rafiee, 2015). An ideal lumped element is not  
130 realizable at lower microwave frequencies because of the associated parasitic reactance caused  
131 by fringing fields. Each component has associated electric and magnetic fields and finite  
132 dissipative loss at RF and microwave frequencies (Rafiee, 2015).

133 Thus, each component stores or releases magnetic and electric energies across them and their  
134 resistance dissipates power (Bahl, 2003).

135 Basic circuit elements (resistance, inductance, and capacitance) with their associated parasitics  
136 are included in Lumped-Element Equivalent Circuit (LEEC) models. The relative measure of the  
137 C, L, and R components in the LEEC depend on the necessary use of the LE. The LEEC model  
138 are used to describe the electrical behavior of the components. For a Computer Aided Design  
139 (CAD) of MICs and MMICs (Leferink, 1995), there is need for a model that is comprehensive.  
140 This constitutes the effect of fringing fields, ground plane, conductor thickness, substrate  
141 material and thickness, associated mounting techniques and applications needed, non-uniform  
142 current distribution. Note that the non-uniform current distribution is caused either by the field  
143 produced by the current itself (skin-effect), the return current (proximity effect) or the current

144 induced in the primary conductor (caused by the field of the return current on the LEs) (Rafiee,  
145 2015).

146 For an accurate modelling of the lumped element, an equivalent circuit representation of the  
147 lumped element LEEC together with its parasitics and the corresponding frequency depending  
148 characteristics are necessary. Thus, a LEEC model includes the required circuit elements to  
149 completely demonstrate its behaviour, particularly its possible resonances. The models can be  
150 completed using mathematical, CAD simulation and measurement based methods. The  
151 component size should be made much smaller as a lumped element is realizable at a dimension  
152 of the wavelength/20 (Bahl, 2003).

## 153 2.1 Equivalent Circuit Modelling of Lumped Inductor

154 Modelling in terms of electrical circuits and numerical equations for each of the components  
155 (interdigital capacitor, pad capacitor, straight line inductor or inductor) of lumped element is  
156 indispensable for a precise quasi lumped element modeling. Thus, as early as 1943, models were  
157 developed for LEs. These models were based on analytical semi empirical equations. Terman, (1943)  
158 was able to publish an expression for the inductance of a thin metallic straight line. The expression  
159 was subsequently improved by Caulton *et al.*, (1968), by adding the metallization thickness.  
160 Wheeler, (1928) published an approximate formula for the inductance of a circular spiral inductor  
161 with reasonably good accuracy at lower microwave frequencies. This formula has been tremendously  
162 used in the design of microwave lumped circuits as stated in equation (2.1). Grover, (2004) discussed  
163 inductance calculations for several geometries. In a lot of the cases, two methods have been used in  
164 the theoretical modeling of microstrip inductors for MICs. The first method is the lumped-element  
165 approach and the second method is the coupled-line approach. The lumped–element approach uses  
166 frequency independent formulae for free-space inductance with ground plane effects. These  
167 frequency-independent formulae are useful only when the total length of the inductor is a little  
168 fraction of the operating wavelength and when inter-turn capacitance can be ignored. In the coupled-  
169 line approach, the multi-conductor coupled microstrip lines are used to analyze an inductor. The later  
170 technique predicts performance reasonably well for up to two turns and frequencies up to 18 GHz  
171 (Bahl, 2003).

172 3-D electromagnetic simulators can be used to determine the accurate characterization of inductors  
173 including the effects of radiation, surface waves, and not excluding the interaction between  
174 components on the performance of densely packed inductors in MMICs (Bahl, 2003).

175 One method that gives an accurate result for a model of lumped inductor is by measuring dc  
176 resistance and S-parameters. Although, they are limited to the device being measured, the equivalent  
177 circuit parameters are extracted from computer optimization and are correlated with the measured dc  
178 resistance and S-parameters data (one or two port data) and are valid up to 26 or 40 GHz depending  
179 on the application.

180

181

182

183

184

185  
186  
187  
188  
189  
190  
191  
192  
193  
194  
195  
196  
197  
198  
199  
200  
201  
202  
203  
204  
205  
206  
207  
208  
209  
210  
211  
212  
213  
214  
215  
216  
217  
218  
219  
220  
221  
222

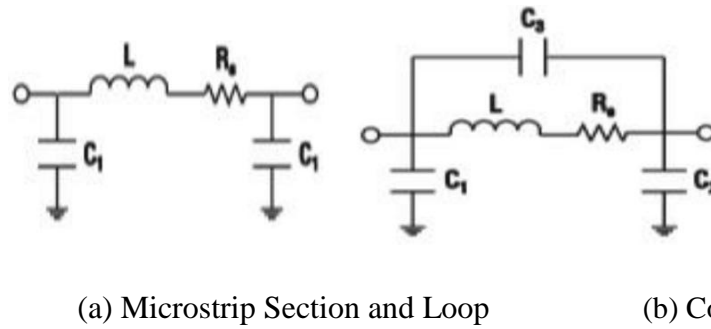


Figure 2.0: Equivalent Circuit Model for Lumped Inductor (Bahl, 2003)

### 2.2.3.2 Equivalent Circuit Modelling of Lumped Capacitor (Interdigital Capacitor)

An interdigital capacitor is a multi finger periodic structure. This multi finger structure consists of fingers that are equally spaced with gaps of equal width in between them. The gaps are very narrow and the capacitance occurs across the interdigital fingers. The gaps are folded to form a long length and use a small amount of space and consequently its attendant relevance has a lumped element. The interdigital capacitor is larger than an overlay capacitor (Bahl, 2003). The structure for an interdigital capacitor is shown in Figure 2.1. The capacitance of the interdigital capacitor can be increased by increasing the number of fingers, putting a thin layer high dielectric constant material between the conductors and the substrate, using an overlay dielectric. This methods increase the interdigital capacitance and the overlay dielectric also acts as a protective shield after fabrication. Interdigital capacitors can be employed with Monolithic Microwave Integrated Circuit (MMIC) designs and Microwave Integrated Circuit (MIC) designs at higher frequency as they can be used instead of the discrete circuit designs. A necessary design consideration for the interdigital capacitor is to keep its size very small in comparison with a wavelength in order for it to possess the characteristics of a lumped element.

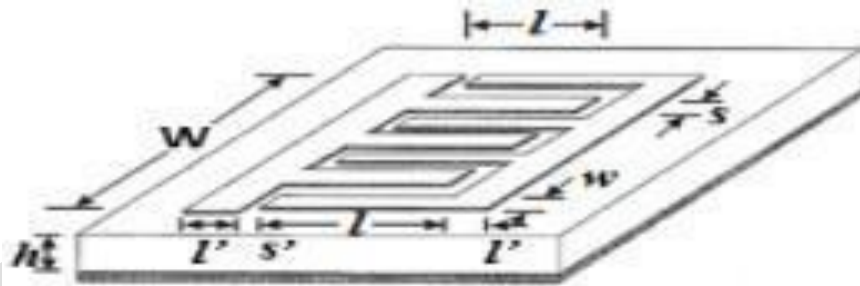


Figure 2.1: Interdigital Capacitor (Bahl, 2003)

To analyze interdigital capacitors, there are four famous techniques. The techniques are approximate analysis, J-inverter network equivalent representation, full wave analysis, and measurement based model. Due to the relevance, comprehensibility, and accuracy (Bahl, 2003) of the first method, it is utilized in this work.

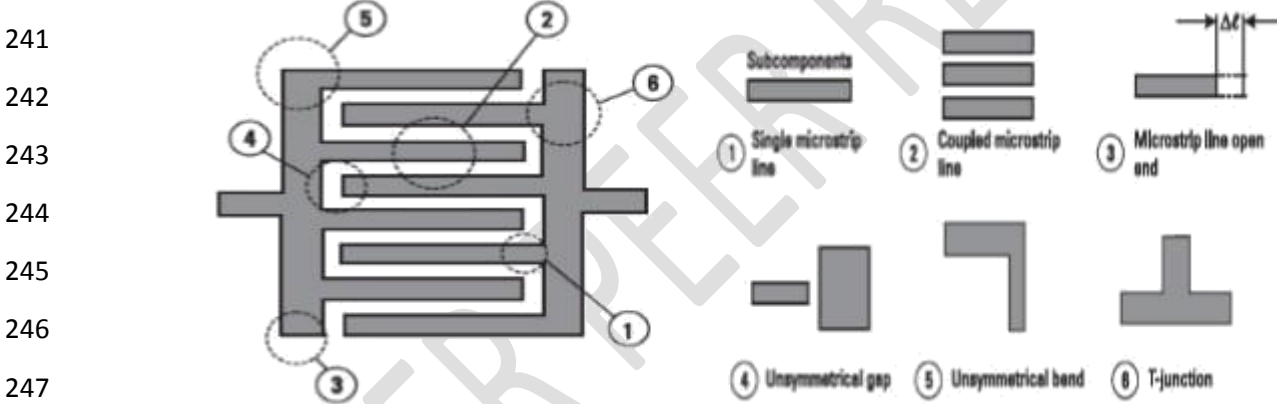
The analysis for the interdigital capacitor using the approximate analysis was based on lossless microstrip coupled line theory (Alley, 1970) and the loss effects were added to make the lossy coupled microstrip lines by representing it with mathematical calculations (Hobdell, 1979).

About four years since Hobdel, (1979) introduced the mathematical calculations; the effect of metallization was added onto the two factors: capacitance and the Q factor (Esfandiari *et al.*, 1983). On the other hand, Alley's theory did not consider different positions of fingers with admittance calculation of parallel shunt fingers.

223 Also, the phase shift along the main line was not considered which was distinct in interdigital  
 224 capacitor with high number of fingers. In addition, the effects of gaps, bends, the T-junctions,  
 225 the open end of microstrip line and discontinuity of the structure were not taken into account. A  
 226 more accurate characterization of these capacitors could be performed if the capacitor geometry  
 227 was divided into basic microstrip sections and subsections (Pettenpaul *et al.*,  
 228 1988).ThePattenpaul *et al.* (1988) publication was based on (Wolff and Kibuuka, 1984) theory.  
 229 This model could therefore be said to provide better accuracy than the previously reported  
 230 analyses. Nonetheless, this method can at best be regarded as an approximate solution rather  
 231 than an explicit or exact. This is due to several assumptions in the grouping of sub-sections and  
 232 as such, could not account for interaction effects between the microstrip sections. This microstrip  
 233 sections and subsections are:

- 234 1. The single microstrip line.
- 235 2. The coupled microstrip lines.
- 236 3. The microstrip open-end discontinuity.
- 237 4. The microstrip unsymmetrical gap.
- 238 5. The unsymmetrical microstrip  $90^\circ$  bend.
- 239 6. The microstrip T-junction discontinuities.

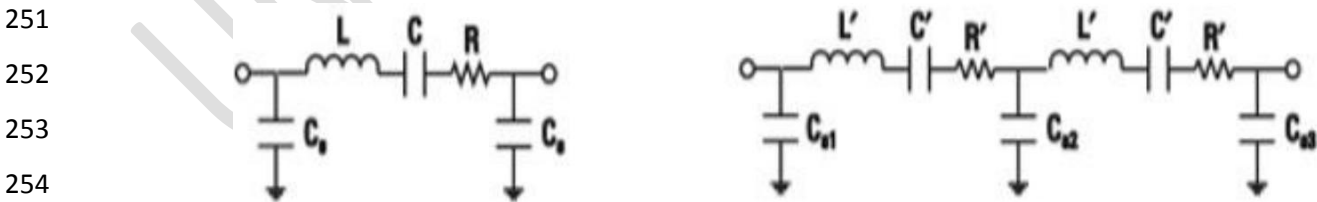
240 These components are shown in Figure 2.2.



248 (a) Interdigital Capacitor (b) Subcomponents

249 Figure 2.2: Lumped Capacitor (Bahl, 2003)

250 The value of the interdigital capacitor can be obtained using equation (2.2)



256 (a) Low Frequency

256 (b) High Frequency

257 Figure 2.3: Lumped Element Equivalent Circuit Models of Interdigital

258 Capacitor (Bahl, 2003).

259 **Numerical Approach:** Although, the equivalent circuit models for the interdigital capacitor and  
 260 inductor can be used to model them, they were explained as not exact and explicit. Equations  
 261 (2.1) through (2.6) can be used to determine the dimensions and resonance frequency required  
 262 for a particular design of the quasi lumped element resonator antenna. However, these are just  
 263 estimates, especially at high frequencies, for designing the circuit and are not accurate. By using  
 264 numerical methods employed via electromagnetic (EM) simulators, the antenna can be simulated  
 265 efficiently and additional features in the layout of the design can be adjusted, it can meet with  
 266 different configurations (2-D or 3-D) and it is versatile.

267 The simulators put into consideration other constraints such as junction discontinuities, substrate  
 268 effects (thickness and dielectric constant). The most common field solver technique employed  
 269 with planar structures is the Method of Moments (MoM) while for 3-D structures, it is more of  
 270 the Finite Element Method (FEM). Both of these techniques function with EM analysis in the  
 271 frequency domain. FEM is used when a more complex design is involved than with MoM and it  
 272 also uses a lot of computation time and requires much more memory. EM analysis in the time  
 273 domain also exists, example of these techniques are Transmission Line Matrix (TLM) method  
 274 and the Finite Difference Time-Domain (FDTD) method.

275 From the literatures, it is now known that the inductor and capacitors are given by

276 i. **Inductor:** The inductor is a single, narrow and straight conductor, which is located at the  
 277 centre finger and shorted across the interdigital capacitor. It is presented in parallel with the  
 278 interdigital capacitor in the circuit diagram for the quasi lumped element resonator antenna  
 279 showed in Figure2.1. The magnitude of the inductor can be increased by using a meander line.  
 280 The equation for determining the value of the inductance of the inductor is given as (Avenhaus,  
 281 1996) :

$$282 \quad L = 200 * 10^{-9} I_L \left( \ln \frac{2 * I_L}{w_1 + t} + 0.50049 + \frac{w_1}{3 * I_L} \right) \quad (2.1)$$

283 where:

284  $L$  is the inductance of the interdigital capacitor,

285  $I_L$  is the inductor length

286  $W_1$  is the inductor width

287  $t$  is the thickness of the resonator

288 ii. **Interdigital capacitor:** It is a structure containing a multi periodic arrangement of  
 289 conductors with equal spacing in between in the form of a multi finger like periodic pattern. This  
 290 structure is associated with the capacitance used by the quasi lumped element resonator antenna. The  
 291 interdigital capacitor is usually in parallel with the inductor in the quasi lumped element resonator  
 292 antenna equivalent circuit (Ain *et al.*, 2013). The approximate value for the interdigital capacitor can  
 293 be calculated (Huang *et al.*, 1999) as follows:

$$294 \quad C = e_o * \frac{e_r + 1}{2} * (N - \Delta) * C_L \quad (2.2)$$

295 where:

296  $C$  is the capacitance of the interdigital capacitor



297  $e_o$  is the permittivity of free spaced  
 298  $e_r$  is the dielectric constant of the substrate  
 299 N is the number of fingers  
 300  $\Delta$  is the correction factor  
 301  $C_L$  is the overlapping length of the interdigital capacitor fingers.

302 iii. **Pad Capacitors:** The pad capacitors are two and are at both sides of the resonator. They  
 303 are represented with  $C_{p1}$  and  $C_{p2}$  as shown on Figure 2.1(b). They act as capacitors to the  
 304 ground and can be adjusted to tune the resonant frequency of the resonator. The respective  
 305 values of  $C_{p1}$  and  $C_{p2}$  do not depend on the number of interdigital fingers or the size of the  
 306 fingers. This is because the location of the ground plane can be adjusted to minimize their  
 307 effects. The two pad capacitors are of the same value and their value can be estimated (Bogatin,  
 308 1988) as:

$$309 \quad C_p = \left[ \frac{2.85 * e_{eff}}{\ln\left(1 + \frac{1}{2} * \left(\frac{8 * h}{w_{eff}}\right) * \left(\frac{8 * h}{w_{eff}}\right) + \sqrt{\left(\frac{8 * h}{w_{eff}}\right)^2 + \pi^2}\right)} \right] * \left[ \frac{l}{25.4 * 10^{-3}} \right] \quad (2.3)$$

310 where:

311  $C_p$  is the pad capacitance  
 312 h is the thickness of the substrate  
 313  $e_{eff}$  is the effective dielectric constant of the substrate  
 314 l is the length of the pad  
 315  $W_{eff}$  is the effective corrected transmission line width

316 i. **Resonant frequency:** The resonant frequency of an antenna is the frequency at which  
 317 electromagnetic waves can be transmitted or received by the antenna. The resonant frequency of  
 318 the quasi lumped element resonator antenna is calculated using the following expression (Ain  
 319 and Hassan, 2004)

$$320 \quad f = \frac{1}{2 * \pi * \sqrt{L * \frac{C_{p1} * C_{p2}}{C_{p1} + C_{p2}} + C}} \quad (2.4)$$

321 where:

322 f is the resonant frequency of the antenna  
 323 L is the inductance of the inductor  
 324  $C_{p1}$ , is the pad capacitance  
 325 C is the capacitance of the interdigital capacitor  
 326 The parameters  $e_{eff}$  and  $w_{eff}$  are expressed mathematically as:

$$327 \quad e_{eff} = \frac{e_r + 1}{2} + \frac{e_r - 1}{2} * \left(1 + 10 * \frac{h}{w}\right)^{-\frac{1}{2}} \quad (2.5)$$

328 
$$w_{eff} = w + \left[ \frac{4 * e}{\sqrt{\left(\frac{t}{h}\right)^2 + \left(\frac{1}{\pi \left(\frac{t}{h} + 1.10\right)}\right)^2}} \right] \quad (2.6)$$

329 where:

330 w is the width of the pad

331 h is the height of the substrate

332 t is the thickness of the conductor

333 e is 2.713

334  $w_{eff}$  is the effective corrected transmission line width

335  $\epsilon_r$  is the dielectric constant of the substrate

336 Given all this parameters, the Quasi lumped element resonator antenna can be designed

### 337 **Conclusion**

338 This paper presented Lumped Elements and its Existence in Quasi Lumped Element Resonator  
 339 Antenna. Lumped Elements was described and the formulas for describing those component  
 340 Lumped Element parts were extracted from literatures. The Quasi Lumped Element Resonator  
 341 Antenna is designed based on some lumped element component parts. Its resonant frequency is  
 342 not proportional to the length of the antenna but the constitution of the lumped elements.

### 343 **References**

- 344 Ain, M., and Hassan, S., (2004). Design of 2 GHz quasi-lumped element oscillator. *Paper*  
 345 *presented at the RF and Microwave Conference, 2004. RFM 2004. Proceedings*, 13-16.
- 346 Ain, M. F., Olokede, S. S., Qasaymeh, Y. M., Marzuki, A., Mohammed, J. J., Sreekantan, S., and  
 347 Abdulla, M. Z., (2013). A novel 5.8 GHz quasi-lumped element resonator antenna. *AEU-*  
 348 *International Journal of Electronics and Communications*, (67(7), 557-563.
- 349 Alley, G. D. (1970). Interdigital capacitors and their application to lumped-element microwave  
 350 integrated circuits. *IEEE Transactions on Microwave Theory and Techniques*, 18(12), 1028-  
 351 1033.
- 352 Bahl, I. J. (2003) *Lumped Elements for RF and Microwave Circuits*: Artech house, pp. 1-6.
- 353 Balanis, C. A. (2016). *Antenna theory: analysis and design*: John Wiley & Sons, pp. 2-7
- 354 Bello, T. M., Usman, A. D., Tekanyi, A. M. S. (2018). Emergence of Defected Ground Structure  
 355 and its effect on Quasi Lumped Element Resonator Antenna. *IOSR Journal of Engineering*  
 356 *(IOSRJEN)*, 8(4), 16-22.

357 Bogatin, E. (1988). Design rules for microstrip capacitance. *IEEE Transactions on components,*  
358 *hybrids, and manufacturing technology, 11(3), 253-259.*

359 Esfandiari, R., Maki, D. W., and Siracusa, M. (1983). Design of interdigitated capacitors and  
360 their applications to gallium arsenide monolithic filters. *IEEE Transactions on Microwave*  
361 *Theory and Techniques 31(1), 57-64.*

362 Hobdel, J. L. (1979). Optimization of interdigital capacitors. *IEEE Transactions on Microwave*  
363 *Theory Techniques, 27, 788-791*

364 Huang, F., Avenhaus, B., Lancaster, M. (1999), Lumped-element switchable semiconducting  
365 filters. *IEEE Proceedings-Microwaves, Antennas and Propagation 146(3), 229-233.*

366 Leferink, F. B. (1995). Inductance calculations: methods and equations. Paper presented at the  
367 Electromagnetic Compatibility, 1995. Symposium Record, 1995 *IEEE International*  
368 *Symposium on, 16-22.*

369 Pattenpaul, E., Kapusta, H., Weisgerber, A., Mampe, H., Luginsland, J., and wolff, I. (1988).  
370 CAD model of lumped element on GaAs up to 18 GHz. *IEEE Transactions on Microwave*  
371 *Theory and Techniques, 36(2), 294-304.*

372 Rafiee, M. (2015). Design and Modeling of a new CPW-Fed Quasi-PIFA Antenna using  
373 Quasi-Lumped Resonator for 4 GHz Handheld devices, Universiti Sains Malaysia pp. 1-30  
374